

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09303

D T-01-09

1S2092

Silicon Epitaxial Planar Type

Diode

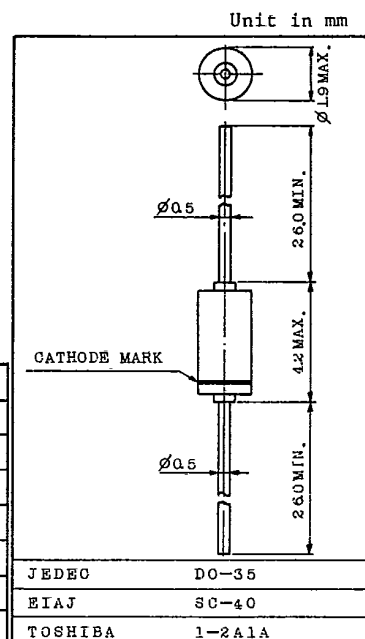
GENERAL PURPOSE DETECTOR AND RECTIFIER APPLICATIONS

FEATURES:

- High Maximum (Peak) Reverse Voltage : $V_{RM}=125V$
- Small Total Capacitance : $C_T=0.7pF$ (Typ.)
- Fast Reverse Recovery Time : $t_{rr}=2ns$ (Typ.)

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

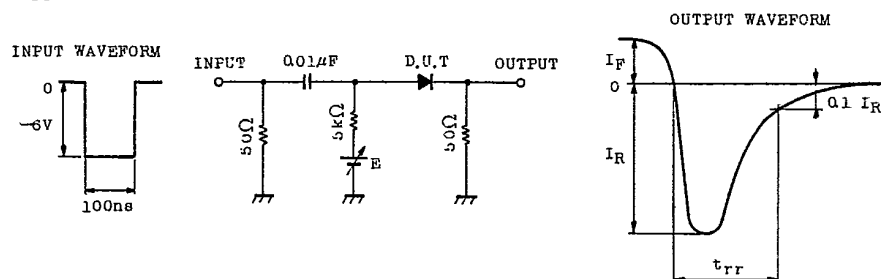
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum(Peak) Reverse Voltage	V_{RM}	125	V
Reverse Voltage	V_R	100	V
Maximum(Peak) Forward Current	I_{FM}	90	mA
Average Forward Current	I_O	30	mA
Surge Current (1 sec)	I_{FSM}	300	mA
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^{\circ}C$



Weight : 0.14g

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Current	I_F	$V_F=1.0V$	4.0	-	-	mA
Reverse Current	I_R	$V_R=100V$	-	-	1.2	μA
Total Capacitance	C_T	$V_R=0, f=1MHz$	-	0.7	3.0	pF
Reverse Recovery Time	t_{rr}	$I_F=10mA$ (Fig.)	-	2	100	ns

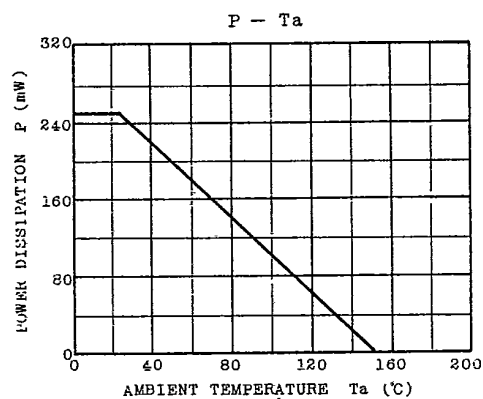
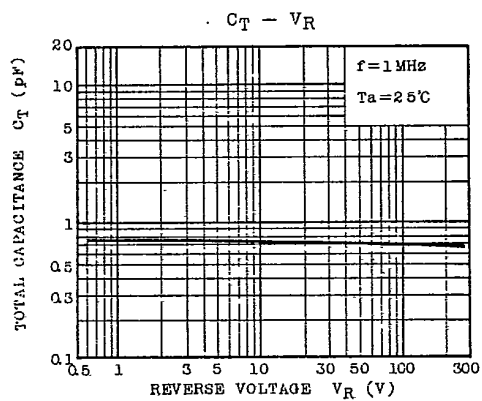
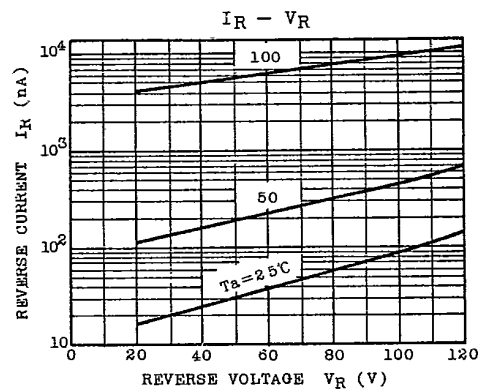
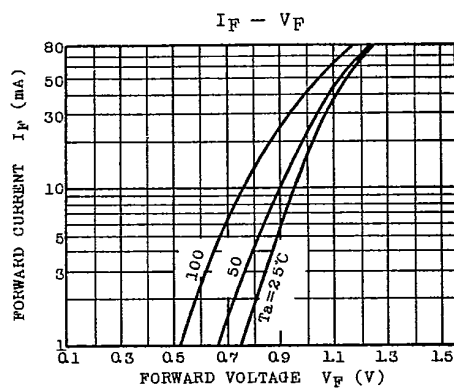
Fig. : t_{rr} TEST CIRCUIT

TOSHIBA CORPORATION

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